| L Number | Hits | Search Text | DB | Time stamp |
|---|---|---|---|---|
| - | 1991 | @ad<=20001221 and 'memory' same 'high voltage' same 'logic' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 11:28 |
| - | 16 | @ad<=20001221 and 'memory' same 'high voltage transistor' same 'logic transistor' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/11 09:03 |
| - | 609 | @ad<=20001221 and 'memory' with 'high voltage' with 'logic' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/10 16:33 |
| - | 488 | @ad<=20001221 and (257/314).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:54 |
| - | 1092 | @ad<=20001221 and (257/315).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:54 |
| - | 148 | @ad<=20001221 and (257/326).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/11 09:02 |
| - | 1441 | @ad<=20001221 and (257/316).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:54 |
| - | 295 | @ad<=20001221 and (257/317).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:54 |
| - | 188 | @ad<=20001221 and (257/318).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:55 |
| - | 1340 | @ad<=20001221 and (438/257-258).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:55 |
| - | 246 | @ad<=20001221 and (438/266).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:55 |
| - | 92 | @ad<=20001221 and (438/242).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:55 |
| - | 53 | @ad<=20001221 and 'memory' and 'HV' adj1 'transistor' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/11 09:22 |
| - | 161 | @ad<=20001221 and (438/201).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/11 09:17 |

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| - | 2 | ("6287907").PN. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/11<br>09:22 |
| - | 2 | ("6037625").PN. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/11<br>09:22 |
| - | 2 | ("6197635").PN. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/11<br>09:23 |
| - | 2 | ("6194270").PN. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/11<br>09:23 |
| - | 2 | ("5904518").PN. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/11<br>09:23 |
| - | 2 | ("4719184").PN. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/11<br>09:23 |
| - | 2 | ("4471373").PN. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/11<br>09:23 |
| - | 256 | @ad<=20001221 and (257/315).ccls. and logic and memory | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/11<br>09:29 |
| - | 14959 | @ad<=20001221 and logic and memory and 'high voltage' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/11<br>09:40 |
| - | 274 | @ad<=20001221 and 'logic' and 'memory cell' and 'high voltage transistor' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/11<br>09:42 |
| - | 44 | @ad<=20001221 and 'memory cell' and 'logic transistor' and 'high voltage transistor' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/11<br>11:06 |
| - | 470 | @ad<=20001221 and 'memory' and 'high voltage transistor' and 'low voltage' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/11<br>11:09 |
| - | 304 | @ad<=20001221 and 'memory cell' and 'high voltage transistor' and 'low voltage' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/11<br>11:35 |
| - | 90 | @ad<=20001221 and 'memory cell' same 'high voltage transistor' same 'low voltage' | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/11<br>11:36 |

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| - | 29 | @ad<=20001221 and 'memory cell' and 'HV transistor' and 'LV' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:57 |
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| - | 223 | @ad<=20001221 and 'memory cell' and 'logic transistor' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/09/11 14:21 |
| - | 2 | "20030168694" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 11:28 |
| - | 218 | @ad<=20001221 and (257/319).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:53 |
| - | 216 | @ad<=20001221 and (257/320).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:53 |
| - | 738 | @ad<=20001221 and (257/321).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:54 |
| - | 204 | @ad<=20001221 and (257/322).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:54 |
| - | 82 | @ad<=20001221 and (257/323).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:54 |
| - | 454 | @ad<=20001221 and (257/324).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:55 |
| - | 109 | @ad<=20001221 and (257/325).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:55 |
| - | 150 | @ad<=20001221 and (257/326).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:55 |
| - | 498 | @ad<=20001221 and (257/314).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:55 |
| - | 1106 | @ad<=20001221 and (257/315).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:56 |
| - | 1453 | @ad<=20001221 and (257/316).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:57 |

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| – | 298 | @ad<=20001221 and (257/317).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:57 |
| – | 193 | @ad<=20001221 and (257/318).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:58 |
| – | 1352 | @ad<=20001221 and (438/257-258).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:59 |
| – | 250 | @ad<=20001221 and (438/266).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:59 |
| – | 94 | @ad<=20001221 and (438/242).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 13:59 |
| – | 46 | @ad<=20001221 and 'memory cell' and 'High voltage transistor' and 'Logic transistor' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 14:00 |
| – | 4 | (("5793673") or ("5792670")).PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 14:00 |
| – | 2 | @ad<=20001221 and 'memory cell' and 'HV' with 'transistor' and 'Logic transistor' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 14:01 |
| – | 45 | @ad<=20001221 and 'memory cell' and 'HV' with 'transistor' and 'LV' with 'transistor' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 14:01 |
| – | 146 | @ad<=20001221 and 'memory cell' and 'high voltage transistor' and 'low voltage transistor' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 16:23 |
| – | 362 | @ad<=20001221 and 'FLOTOX' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 15:13 |
| – | 0 | @ad<=20001221 and 'EPPROM' and 'high voltage transistor' and 'low voltage transistor' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 16:24 |
| – | 10 | @ad<=20001221 and 'EEPPROM' and 'high voltage transistor' and 'low voltage transistor' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 16:25 |
| – | 0 | @ad<=20001221 and 'EEPPROM' and 'HV' and 'LV' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/03/30 16:26 |

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| - | 21 | @ad<=20001221 and 'flash memory' and 'HV' and 'LV' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/03/30 16:26 |
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